



**CHENMKO ENTERPRISE CO.,LTD**

**BAS40CDWPT**

*Lead free devices*

**SURFACE MOUNT**  
**SCHOTTKY DIODE ARRAY**

**VOLTAGE 40 Volts CURRENT 0.2 Ampere**

**APPLICATION**

\* Ultra high speed switching

**FEATURE**

- \* Small surface mounting type. (SC-88/SOT-363)
- \* High speed. ( $T_{RR}=2.5nSec$  Typ.)
- \* Suitable for high packing density.
- \* Maximum total power dissipation is 200mW.
- \* Peak forward current is 300mA.
- \* Schottky diode array ( Dual common cathode ).

**CONSTRUCTION**

\* Silicon epitaxial planar

**WEIGHT**

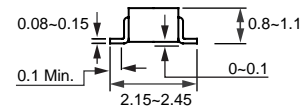
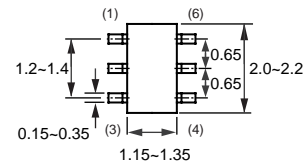
\* 0.008 grams ( Approx. )

**MARKING**

\* CD2



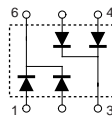
**SC-88/SOT-363**



Dimensions in millimeters

**SC-88/SOT-363**

**CIRCUIT**



RATINGS	SYMBOL	BAS40CDWPT	UNITS
Maximum Recurrent Peak Reverse Voltage	$V_{RRM}$	40	Volts
Maximum RMS Voltage	$V_{RMS}$	28	Volts
Maximum DC Blocking Voltage	$V_{DC}$	40	Volts
Maximum Average Forward Rectified Current	$I_o$	0.2	Amps
Peak Forward Surge Current at 1Sec.	$I_{FSM}$	0.6	Amps
Typical Junction Capacitance between Terminal (Note 1)	$C_J$	5.0	pF
Maximum Reverse Recovery Time (Note 2)	$T_{RR}$	5.0	nSec
Maximum Operating Temperature Range	$T_J$	-55 to +125	°C
Storage Temperature Range	$T_{STG}$	-65 to +150	°C

**ELECTRICAL CHARACTERISTICS** ( At  $T_A = 25^{\circ}C$  unless otherwise noted )

CHARACTERISTICS	SYMBOL	BAS40CDWPT	UNITS
Maximum Instantaneous Forward Voltage	@ $I_F = 1.0mA$	380	mVolts
	@ $I_F = 40mA$	1000	
Maximum Average Reverse Current at $V_R = 30V$	$I_R$	200	nAmps

- NOTES : 1. Measured at 1.0 MHz and applied reverse voltage of 0.0 volts.  
 2. Measured at applied forward current of 10mA and reverse current of 10mA.  
 3. ESD sensitive product handling required.

## RATING CHARACTERISTIC CURVES ( BAS40CDWPT )

FIG. 1 - FORWARD CHARACTERISTICS

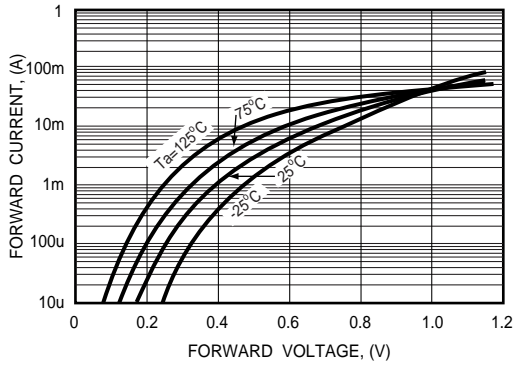


FIG. 2 - REVERSE CHARACTERISTICS

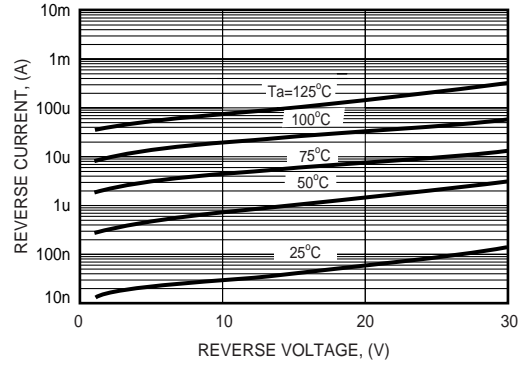


FIG. 3 - TYPICAL JUNCTION CAPACITANCE

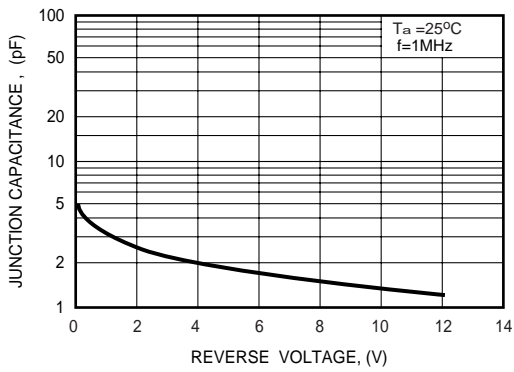


FIG. 4 - TYPICAL FORWARD CURRENT DERATING CURVE

